

## 1、Description

Designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

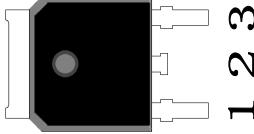
## 2、Applications

- Motor control
- Industrial and domestic lighting
- Heating
- Static switching

## 3、Features

- Blocking voltage to 600 V
- On-state RMS current to 8 A
- Ultra low gate trigger current
- Low cost package.

## 4、Pinning information

PIN	Description	Simplified outline	Symbol
1	main terminal 1(T1)	 TO-252	
2	main terminal 2(T2)		
3	gate (G)		
tab	main terminal T2		

## 5、Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
$V_{DRM}$ $V_{RRM}$	Repetitive peak off-state voltages	600	V
$I_{T(RMS)}$	RMS on-state current	8	A
$I_{TSM}$	Non-repetitive peak on-state current	80	A

## 6、Thermal characteristics

SYMBOL	PARAMETER	Value	UNIT
$R_{th(j-c)}$	junction to case(AC)	4.0	°C/W

## 7. Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{DRM}$	Repetitive peak off-state voltages		-	600	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz (TC = 110°C)	-	8	A
$I_{TSM}$	Non-repetitive peak Surge current	One Full cycle, 60 Hz, $T_J = +110^\circ\text{C}$	-	80	A
$I^2t$	$I^2t$ for fusing	$t = 8.3\text{ms}$	-	32	$\text{A}^2\text{s}$
$I_{GM}$	Peak gate current	Pulse Width $\leq 1.0 \mu\text{s}$ , TC = 85°C	-	4	A
$P_{GM}$	Peak gate power	Pulse Width $\leq 1.0 \mu\text{s}$ , TC = 85°C	-	5	W
$P_{G(AV)}$	Average gate power	Pulse Width $\leq 1.0 \mu\text{s}$ , TC = 85°C	-	1	W
$T_{stg}$	Storage temperature		-40	150	$^\circ\text{C}$
$T_j$	Operating junction temperature		-40	125	$^\circ\text{C}$

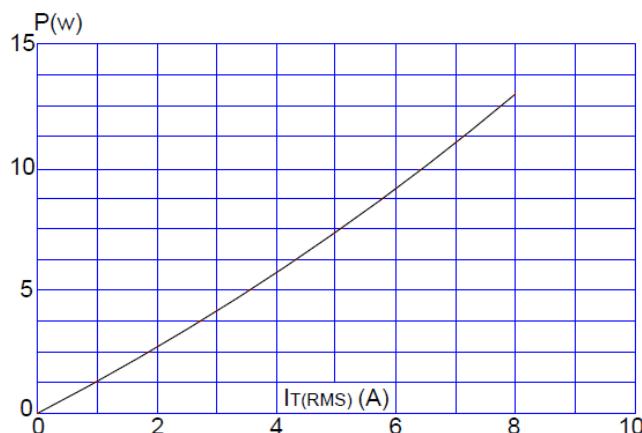
## 8. Characteristics

$T_J = 25^\circ\text{C}$  unless otherwise stated

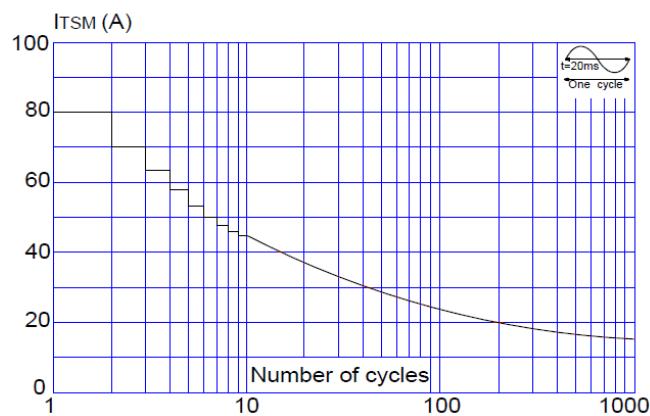
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
<b>Static characteristics</b>						
$I_{GT}$	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1\text{A}$ T2+ G+ T2+ G- T2- G-	-	-	10	mA
$I_L$	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1\text{A}$ T2+ G+ T2+ G- T2- G-	-	-	20	mA
$I_H$	Holding current	Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current $\leq 1 \text{ Adc}$ $T_J = 25^\circ\text{C}$	-	-	15	mA
$V_{TM}$	On-state voltage	$I_{TM} = 11\text{A}, t_p=380\mu\text{s}$	-	-	1.7	V
$V_{GT}$	Gate trigger voltage (Continuous dc)	Main Terminal Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$ , $T_J = -40^\circ\text{C}$ All Quadrants	-	-	1.5	V
$V_{GD}$	Gate Non-Trigger Voltage	$V_D=V_{DRM}$ $T_J=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	0.2	-	-	V
<b>Dynamic Characteristics</b>						
$dV/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(\text{max})}$ ; $T_J = 125^\circ\text{C}$ ; Exponential wave form; $RGK=1\text{K}\Omega$	100	-	-	$\text{V}/\mu\text{s}$

## 9. Electrical Characteristics Curve

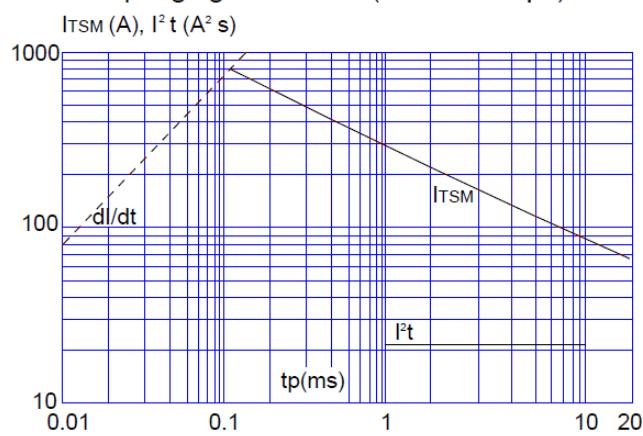
**FIG.1** Maximum power dissipation versus RMS on-state current



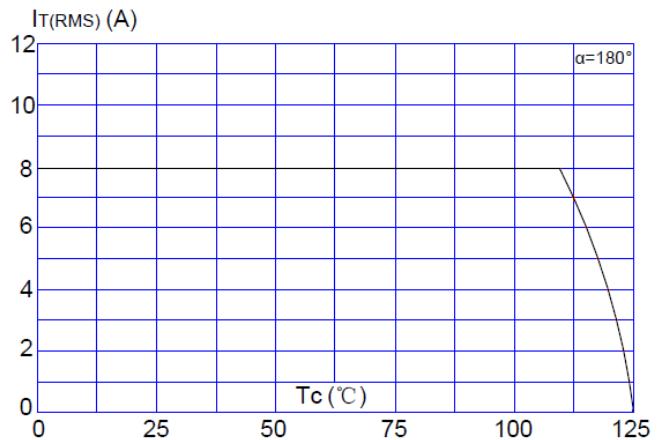
**FIG.3:** Surge peak on-state current versus number of cycles



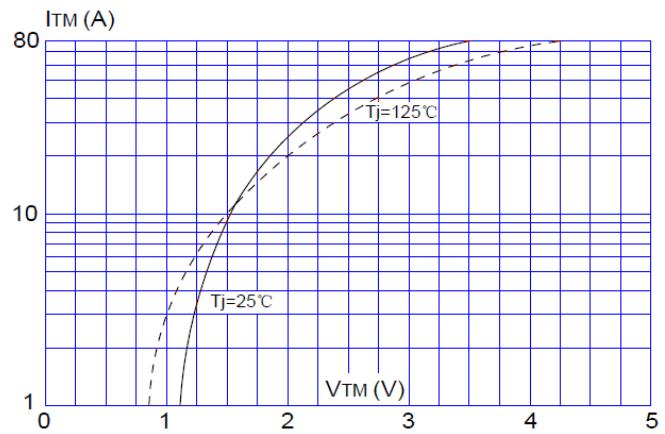
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 50\text{A}/\mu\text{s}$ )



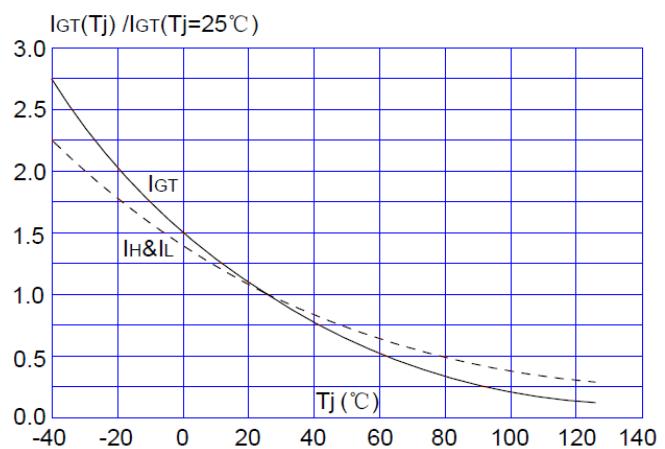
**FIG.2:** RMS on-state current versus case temperature



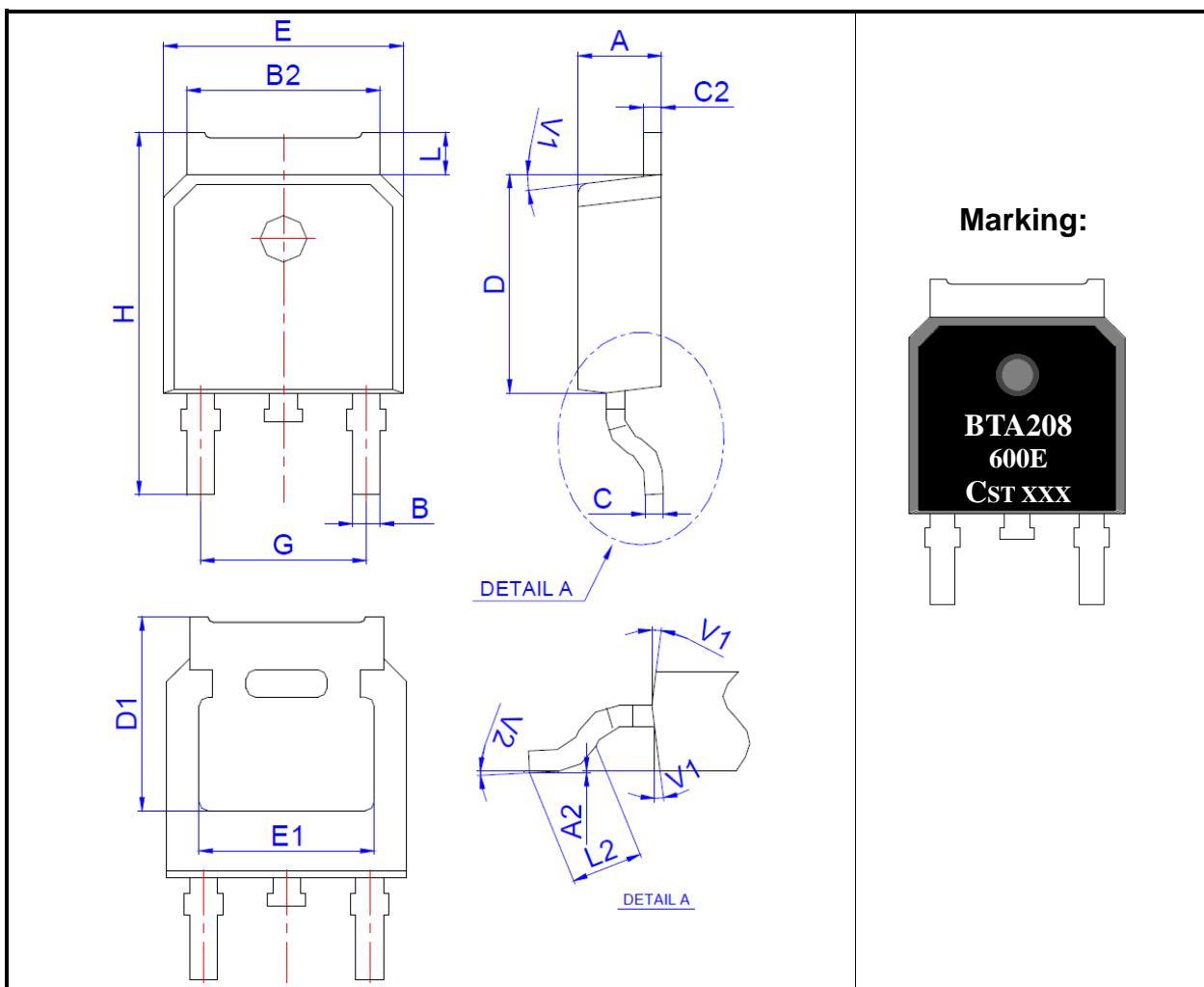
**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



## 10、Package outline(TO-252)



DIM	Inches			Milimeters		
	Min	Type	Max	Min	Type	Max
A	0.083	-	0.098	2.10	-	2.50
A2	0.001	-	0.009	0.03	-	0.23
B	0.026	-	0.034	0.66	-	0.86
B2	0.202	-	0.216	5.18	-	5.48
C	0.016	-	0.024	0.40	-	0.60
C2	0.017	-	0.023	0.44	-	0.58
D	0.232	-	0.248	5.90	-	6.30
D1		0.209REF			5.30REF	
E	0.252	-	0.268	6.40	-	6.80
E1	0.182			4.63		
G	0.176	-	0.184	4.47	-	4.67
H	0.374	-	0.421	9.50	-	10.70
L	0.043	-	0.048	1.09	-	1.21
L2	0.053	-	0.065	1.35	-	1.65
V1		7°			7°	
V2	0°		6°	0°		6°

CST